

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	103	(micro\$1len.or (micro adj len)) same.((thin adj film.adj transistor) or TFT)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/12 08:42
L2	81	1 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/12 08:43
L3	3	("6215542" "6466288" "6525797").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/12 09:07
L4	69	Kaise-Kikuo.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/12 10:40
L5	23	Shinoda-Kazuhiro.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/12 10:41
L6	40	Abe-Moriaki.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/12 10:41
L7	122	4 or 5 or 6	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/12 10:41
S10	2347	(sulfuric or H2SO4 or "H.sub.2 SO. sub.4") with spray\$3	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 09:19
S11	29	S10 and capacitor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 09:31
S12	192	S10 and semiconductor	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 09:31
S13	175	S12 not S11	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 09:31
S14	99	S13 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 09:37
S15	1	"6509278".pn. and titanium	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 11:14
S16	1182	438/745.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 11:14

S17	198	438/747.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 11:14
S18	184	438/748.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 11:14
S19	405	438/754.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 14:05
S20	405	438/754.ccls.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 14:05
S21	17443	(micro\$1len or len) and (polish or polishing or planarize\$1 or planarizing or cmp)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 16:59
S22	6599	S21 and (resist or photo\$1resist or photo\$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:16
S23	4978	S22 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:51
S24	2584	S23 and transparent	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:51
S25	2071	S24 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:51
S26	825	S25 and (high\$1k or alumina or (aluminum adj oxide) or "Al.sub.2 O.sub.3" or "HfO.sub.2" or "Ta. sub.2 O.sub.5" or tantalum or "Nb.sub.2 O.sub.5" or "ZrO.sub. 2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:18
S27	487	S26 and (transistor or TFT)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:53
S28	364	S27 and (transparent with (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:55
S29	53	S28 and (micro\$1len or (micro adj len))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 12:55
S30	1	("6469832").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 13:05

S31	9	("20010012596" "20020012088" "20020021386" "20020027715" "4588261" "5056912" "5715022" "6129866" "6336406").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 13:06
S32	4	(micro\$1len) and (polish or polishing or planarize\$1 or planarizing or cmp)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:15
S33	642	(micro\$1len or (micro adj len)) and (polish or polishing or planarize\$1 or planarizing or cmp)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:15
S34	369	S33 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:15
S35	291	S34 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:16
S36	238	S35 not S29	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 13:16
S37	200	S36 and (resist or photo\$1resist or photo\$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:18
S38	1	"6469832".pn.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 14:26
S39	5364	(micro\$1len or len) same (polish or polishing or planarize\$1 or planarizing or cmp)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:17
S40	1838	S39 and transparent	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:17
S41	607	S40 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:17
S42	555	S41 not S37	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:18
S43	457	S42 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:18
S44	147	S43 and (high\$1k or alumina or (aluminum adj oxide) or "Al.sub.2 O.sub.3" or "HfO.sub.2" or "Ta.sub.2 O.sub.5" or tantalum or "Nb.sub.2 O.sub.5" or "ZrO.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 15:19

S45	4	("5306926" "5706065" "5844290" "6632342").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 15:27
S46	11	("4553153" "4667092" "4694185" "4966831" "5293267" "5306926" "5321249" "5321297" "5324930" "5371397" "5505804").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 16:33
S47	1	"6211916".pn. and transparent	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 16:54
S48	1	"5824236".pn. and transparent	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/09 16:59
S49	64171	(micro\$1len or len) and (resist or photo\$1resist or photo\$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 16:59
S50	3110	S49 and ((thin adj film adj transistor) or TFT)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:06
S51	336	S50 and (micro\$1len or (micro adj len\$1))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:01
S52	277	S51 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:02
S53	209	S52 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:02
S54	356	S49 and (((thin adj film adj transistor) or TFT) same (lens or micro\$1len))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:07
S55	210	S54 and (etch or etching) and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:07
S56	51	S53 and S55	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:46
S57	782	216/24.CCLS.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:46
S58	166	216/26.CCLS.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/09 17:46